

200V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information			
Device	Marking		
CS18N20BF	TO-220F	CS18N20BF	
CS18N20BP	TO-220	CS18N20BP	

TO-220F GDS	TO-220 GDS
	Go

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted				
Parameter	Symbol	Va	Unit	
		TO-220F	TO-220	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	200		V
Continuous Drain Current	I _D	18		A
Pulsed Drain Current (note1)	I _{DM}	72		A
Gate-Source Voltage	V _{GSS}	±.	20	V
Single Pulse Avalanche Energy (note2)	E _{AS}	231.9		mJ
Avalanche Current (note1)	I _{AS}	6.7		A
Repetitive Avalanche Energy (note1)	E _{AR}	139		mJ
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	63.7	104	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C

Thermal Resistance				
Peremeter	Symbol	Valu	Unit	
Parameter		TO-220F	TO-220	- Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	1.96	1.2	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	K/W



CS18N20BF,CS18N20BP

Specifications $T_J = 25^{\circ}C$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			11
Falameter	Symbol	Test conditions	Min.	Тур.	Max.	Unit
Static			-	-		
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 250\mu A$	200			V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 200V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 20 V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.0		4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 9A$		0.12	0.15	Ω
Dynamic						
Input Capacitance	C _{iss}	– V _{GS} = 0V,		882		pF
Output Capacitance	C _{oss}	$V_{DS} = 25V,$		166		
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		91		
Total Gate Charge	Q _g			56		nC
Gate-Source Charge	Q _{gs}	$V_{DD} = 160V, I_D = 18A, V_{GS} = 10V$		6		
Gate-Drain Charge	Q_{gd}			30		
Turn-on Delay Time	t _{d(on)}			38.5		
Turn-on Rise Time	t _r	V _{DD} = 100V, I _D =18A,		47		
Turn-off Delay Time	t _{d(off)}	$R_{\rm G} = 25 \ \Omega$		245		ns
Turn-off Fall Time	t _f			70		
Drain-Source Body Diode Character	istics					
Continuous Body Diode Current	۱ _s	– T _C = 25 °C			18	٨
Pulsed Diode Forward Current	I _{SM}				72	A
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C, I_{SD} = 9A, V_{GS} = 0V$			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 18A, di _F /dt =100A /μs		182		ns
Reverse Recovery Charge	Q _{rr}			1.27		μC

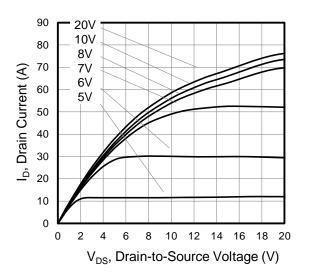
Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)





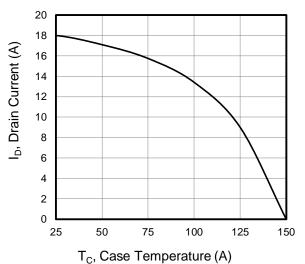
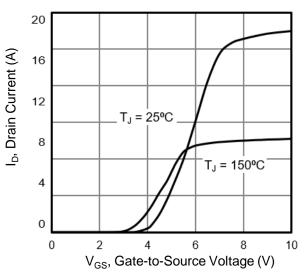


Figure 5. Transfer Characteristics



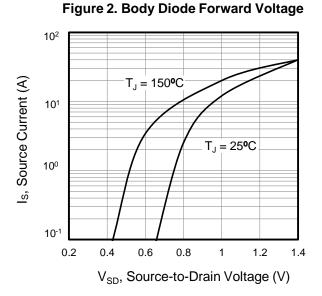


Figure 4. BV_{DSS} Variation vs. Temperature

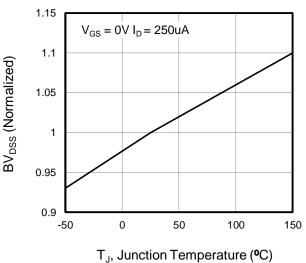
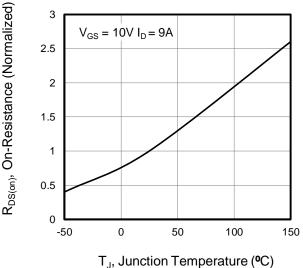
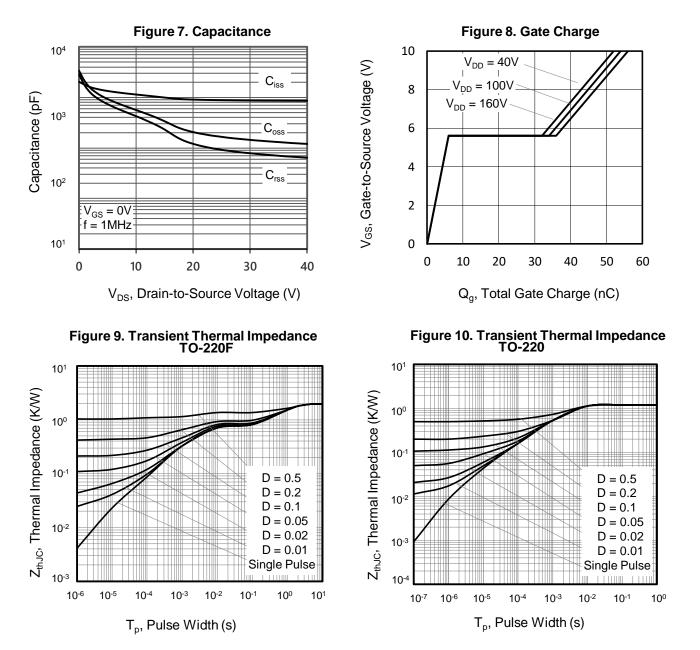


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted







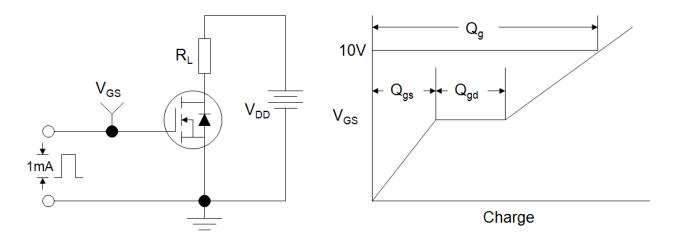


Figure B: Resistive Switching Test Circuit and Waveform

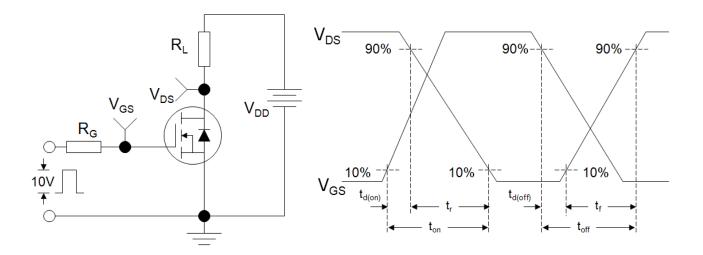
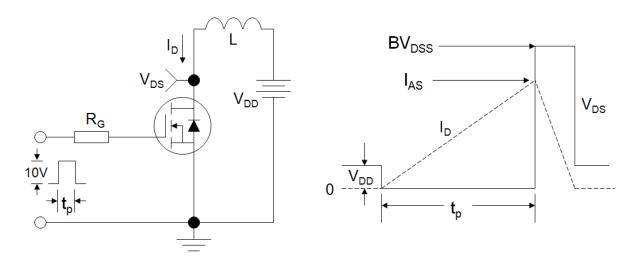


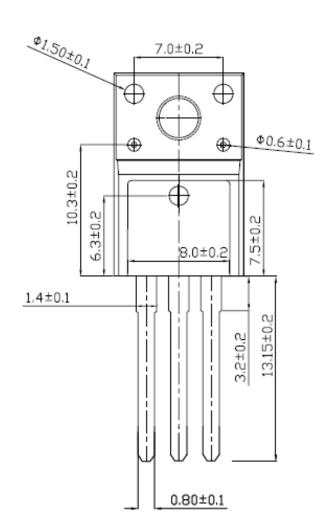
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

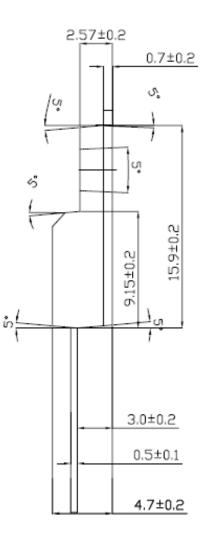






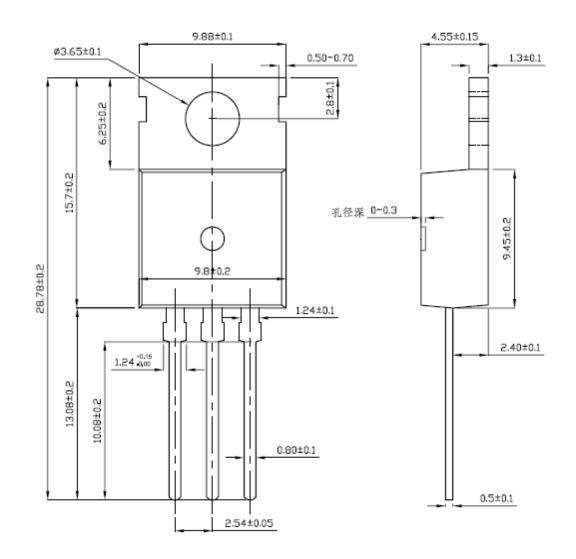
TO-220F







TO-220





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